

**Notice of References Cited**

Application/Control No.

09/584,601

Applicant(s)/Patent Under  
Reexamination  
EISENBEISER ET AL

Examiner

Scott R. Wilson

Art Unit

2826

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-			
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	K	US-			
	L	US-			
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

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	U	IDS Reference CM: "GaInAs Superconducting FET", IBM Technical Bulletin, vol. 36 no.8 Aug 1993, p.655.			
	V	IDS Reference DP: "Formation of Si Epi./MgO-Al <sub>2</sub> O <sub>3</sub> Epi./SiO <sub>2</sub> /Si and Its Epitaxial Film Quality, Masao Mikami et al., Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34.			
	W	IDS Reference DR: "Reaction and Regrowth control of CeO <sub>2</sub> on Si(111) surface for the silicon-on-insulator structure", T. Chikyow et al., Appl. Phys. Lett. 65(8), 22 August 1994, pp. 1030-1032.			
	X	"Reactions at the interfaces of thin films of Y-Ba-Cu- and Zr-oxides with Si substrates", D. B. Fenner et al., J. Appl. Phys., 69(4), 15 Feb. 1991.			

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

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	U	"Low temperature growth of CeO <sub>2</sub> (111) layer on Si(100) using dual plasma deposition", L. P. Wang et al., Materials Science and Engineering A308 (2001) p. 176-179
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Ref. 09/584601

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Applicant(s)

CR00-001

Examiner

Group Art Unit

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B	6,023,082	2/2000	McKee et al <i>SPW</i>	257	295
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X		